

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

- 1-24. (Canceled)
25. (New) A method for fabricating a semiconductor circuit module, the method comprising:
- providing circuit devices, each having a contact area on a front side thereof;
 - applying a patterned connection layer to a transfer substrate;
 - applying the front sides of the circuit devices to the patterned connection layer;
 - applying a filler between the circuit devices;
 - removing the transfer substrate; and
 - applying an electrical connection device to connect the circuit devices.
26. (New) The method according to claim 25, further comprising applying a protection layer at least partially covering the electrical connection device.
27. (New) The method according to claim 26, further comprising providing a second electrical connection device in a region not covered by the protection layer.
28. (New) The method according to claim 25, wherein applying the patterned connection layer comprises printing the patterned connection layer on the transfer substrate.

29. (New) The method according to claim 25, further comprising arranging said circuit devices on said patterned connection layer, such that the contact areas of said circuit devices are not located on said patterned connection layer.

30. (New) The method according to claim 25, further comprising curing said patterned connection layer after applying said circuit devices.

31. (New) The method according to claim 25, further comprising providing an encapsulation layer on backsides of said circuit devices.

32. (New) The method according to claim 25, wherein applying the filler comprises selecting a process from the group consisting of casting and printing.

33. (New) The method according to claim 31, wherein applying the encapsulation layer comprises selecting a process from the group consisting of casting and printing.

34. (New) The method according to claim 25, further comprising curing said filler before removing said transfer substrate.

35. (New) The method according to claim 31, further comprising curing said encapsulation layer before removing said transfer substrate.

36. (New) The method according to claim 25, further comprising providing a conductive layer, providing an insulating layer separating the electrical connection device from the conductive layer, and

providing an electrical connection between said conductive layer and said electrical connection device.

37. (New) A semiconductor circuit module comprising
circuit devices, each having a contact area on a front side thereof,
a patterned connection layer connected to the front sides of the circuit devices,
a filler between the circuit devices, and
an electrical connection device connecting the circuit devices.
38. (New) The semiconductor circuit module of claim 37, further comprising
a protection device covering at least part of the electrical connection device.
39. (New) The semiconductor circuit module of claim 37, further comprising
a second electrical connection device in a region not covered by the protection device.
40. (New) The semiconductor circuit module of claim 37, wherein
said circuit devices comprise functional circuit devices.
41. (New) The semiconductor circuit module of claim 37, further comprising
an encapsulation layer at least partially covering backsides of the circuit devices.
42. (New) The semiconductor circuit module of claim 37, wherein
said patterned connection layer comprises a dielectric material.
43. (New) The semiconductor circuit module of claim 42, wherein
said dielectric material comprises a material selected from the group consisting of
a polymer, an epoxy resin, an adhesive, a silicone, and a polyamide.

44. (New) The semiconductor circuit module of claim 37, wherein said filler comprises a curable insulator.
45. (New) The semiconductor circuit module of claim 44, wherein said curable insulator comprises a material selected from the group consisting of a polymer, an adhesive, and a silicone.
46. (New) The semiconductor circuit module of claim 41, wherein said filler layer and said encapsulation layer are the same material.
47. (New) The semiconductor circuit module of claim 37, further comprising a conductive layer,
an insulating layer separating said conductive layer from said electrical connection device, and
an electrical connection connecting said conductive layer to said electrical connection device.
48. (New) The semiconductor circuit module of claim 38, further comprising a non-conductive passivation layer on said protection device.
49. (New) A stack comprising
a first circuit module as recited in claim 38,
a conductive passage, and
a second circuit module as recited in claim 38, said second circuit module being connected to the first circuit module by a conductive adhesive.
50. (New) The semiconductor circuit module of claim 40, wherein said second electrical connection device comprises an edge connector.

51. (New) The semiconductor circuit module of claim 40, wherein said second electrical connection device comprises a soldering pad in electrical communication with a solder ball.

52. (New) The semiconductor circuit module of claim 38, wherein said semiconductor circuit module has a thickness less than 200 μm .